

General Description

The WSK180N04 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK180N04 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

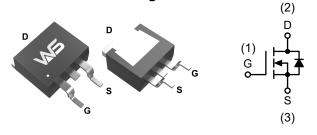
Product Summery

BVDSS	RDSON	ID
40V	3.0mΩ	180A

Applications

- Switching application
- Power Management for Inverter Systems.

TO-263-2L Pin Configuration



Symbol	Parameter	Rating	Unit		
Common	Ratings (T _c =25°C Unless Otherwise Noted)			P	
V _{DSS}	Drain-Source Voltage	40	v		
V_{GSS}	Gate-Source Voltage	±20	v		
TJ	Maximum Junction Temperature		175	°C	
T _{STG}	Storage Temperature Range	-55 to 175	°C		
I _S	Diode Continuous Forward Current	T _C =25℃	176	А	
Mounted o	on Large Heat Sink	·	•		
I _{DM}	Pulsed Drain Current *	T _C =25℃	648 ^{1,2}	А	
I _D	Continuous Drain Current	T _C =25℃	180	Α	
	Continuous Drain Current	T _C =100°C	120		
P_D	Maximum Rower Dissingtion	T _C =25℃	192	W	
	Maximum Power Dissipation	T _C =100°C	96		
$R_{ extsf{ heta}JC}$	Thermal Resistance-Junction to Case		0.78		
$R_{ ext{ heta}JA}$	Thermal Resistance-Junction to Ambient	62.5			
Avalanche	Ratings			•	
E _{AS}	Avalanche Energy, Single Pulsed	L=0.5mH	1.09 ^{1,2}	J	

NOTE: 1,Repetitive rating ; pulse width limited by junction temperatur

2, Drain current is limited by junction temperature



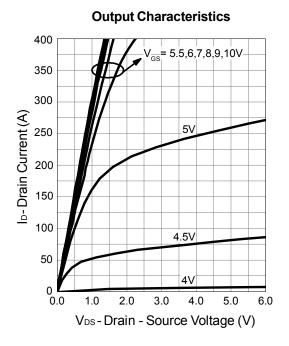
Electrical Characteristics (T_J=25 $^{\circ}$ C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Static Ch	aracteristics					р
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, Ι _{DS} =250μΑ	40	-	-	V
1	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1	۵
I _{DSS}		T_=85℃	-	-	10	μΑ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=250\mu A$	2.0	3.0	4.0	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =88A	-	3.0	3.6	mΩ
Diode Cha	racteristics					
V _{SD} *	Diode Forward Voltage	I _{SD} =88A, V _{GS} =0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =88A, dI _{SD} /	-	27	-	ns
Q _{rr}	Reverse Recovery Charge	dt=100A/μs	-	50	-	nC
Dynamic (Characteristics		1			
R_G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V,	-	4426	-	pF
C _{oss}	Output Capacitance	$V_{DS}=25V$,	-	1027	-	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	537	-	
t _{d(ON)}	Turn-on Delay Time		-	27	-	
Tr	Turn-on Rise Time		-	18	-	ns
$t_{d(OFF)}$	Turn-off Delay Time	$I_{DS} = 88A, V_{GS} = 10V$,	-	41	-	
T _f	Turn-off Fall Time		-	53	-	
Gate Char	ge Characteristics					
Qg	Total Gate Charge		-	121	-	
Q _{gs}	Gate-Source Charge	──V _{DS} =32V, V _{GS} =10V, I _{DS} =88A	-	28	-	nC
Q _{gd}	Gate-Drain Charge		-	34	-	

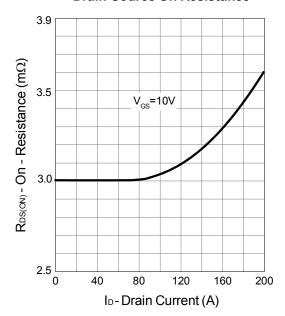
Note * : Pulse test ; pulse width \leq 300µs, duty cycle \leq 2%.

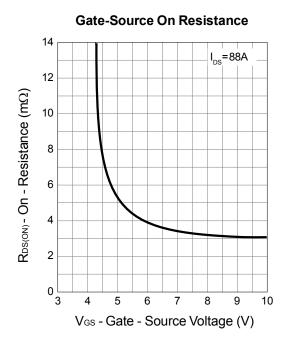


Typical Characteristics

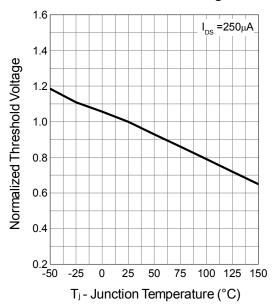


Drain-Source On Resistance



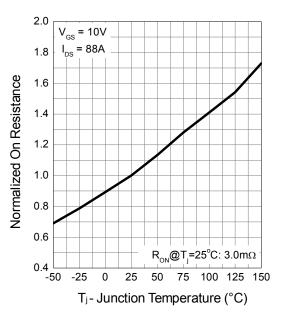


Gate Threshold Voltage





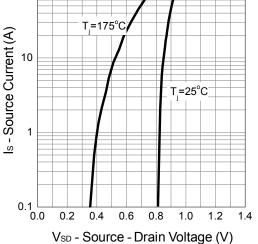
Typical Characteristics



Drain-Source On Resistance

200 100 T_i=175°C

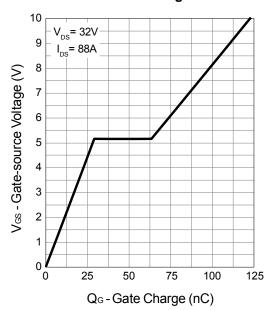
Source-Drain Diode Forward



12000 Frequency=1MHz 10500 9000 Ciss Coss 1500 Crss 0 L 0 8 16 24 32 40 VDS - Drain - Source Voltage (V)

Capacitance

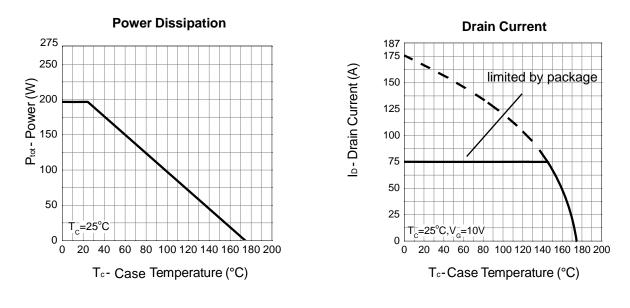
Gate Charge





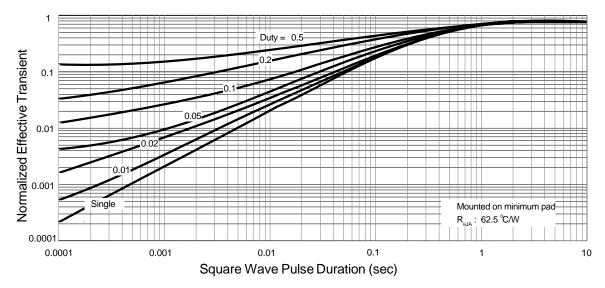
WSK180N04

N-Ch MOSFET



Safe Operation Area 1000 "Linni 100us Ip- Drain Current (A) 100 10ms 1ms 10 DC 1 0.1 10 100 400 1 V_{DS} - Drain - Source Voltage (V)



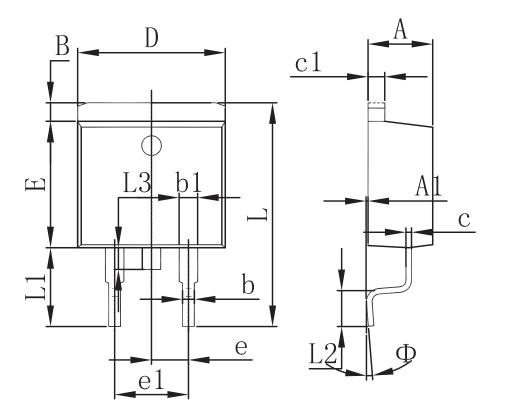


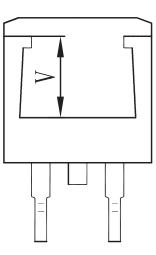


WSK180N04

N-Ch MOSFET

Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Φ	0°	8°	0°	8°	
V	5.600	REF.	0.220REF.		



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